

# DATA SHEET

For a complete data sheet, please also download:

- The IC04 LOCMOS HE4000B Logic Family Specifications HEF, HEC
- The IC04 LOCMOS HE4000B Logic Package Outlines/Information HEF, HEC

## **HEF4750V** **LSI** Frequency synthesizer

Product specification  
File under Integrated Circuits, IC04

January 1995

## Frequency synthesizer

**HEF4750V**  
**LSI**

### DESCRIPTION

The HEF4750V frequency synthesizer is one of a pair of LOC MOS devices, primarily intended for use in high-performance frequency synthesizers, e.g. in all communication, instrumentation, television and broadcast applications. A combination of analogue and digital techniques results in an integrated circuit that enables high performance. The complementary device is the universal divider type HEF4751V.

Together with a standard prescaler, the two LOC MOS integrated circuits offer low-cost single loop synthesizers with full professional performance. Salient features offered (in combination with HEF4751V) are:

- Wide choice of reference frequency using a single crystal.
- High-performance phase comparator — low phase noise — low spuri.
- System operation to > 1 GHz.
- Typical 15 MHz input at 10 V.
- Flexible programming:
  - frequency offsets
  - ROM compatible
  - fractional channel capability.
- Programme range  $6\frac{1}{2}$  decades, including up to 3 decades of prescaler control.
- Division range extension by cascading.
- Built-in phase modulator.
- Fast lock feature.
- Out-of-lock indication.
- Low power dissipation and high noise immunity.

### APPLICATION INFORMATION

Some examples of applications for the HEF4750V in combination with the HEF4751V are:

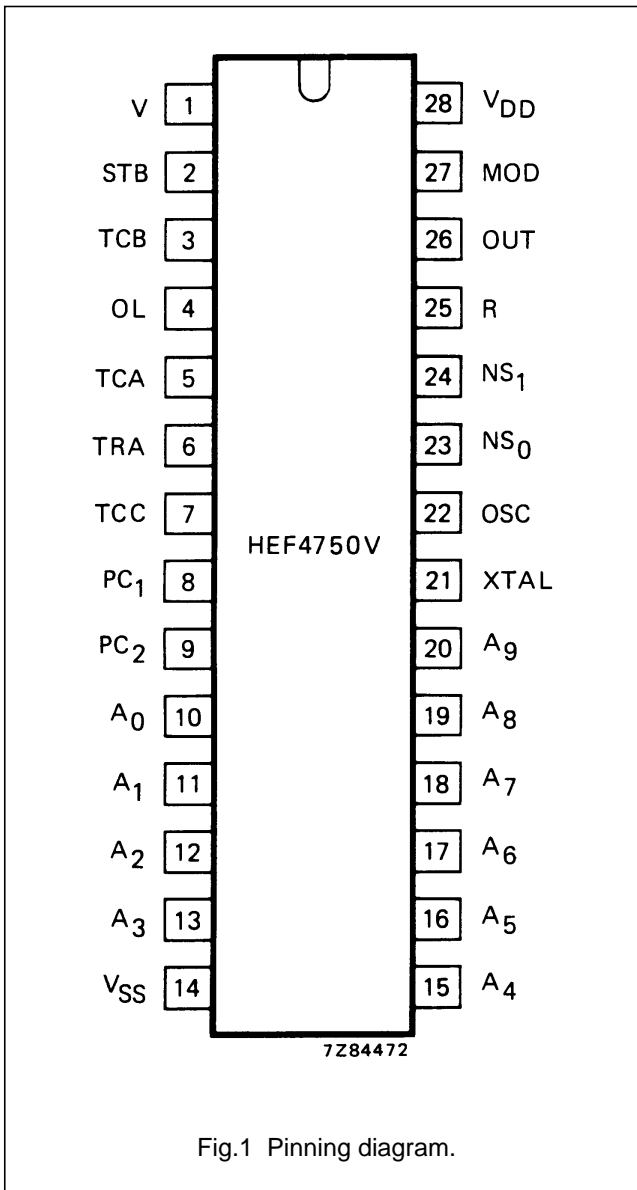
- VHF/UHF mobile radios.
- HF s.s.b. transceivers.
- Airborne and marine communications and nav aids.
- Broadcast transmitters.
- High quality radio and television receivers.
- High performance citizens band equipment.
- Signal generators.

### SUPPLY VOLTAGE

RATING	RECOMMENDED OPERATING
-0,5 to +15	9,5 to 10,5 V

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**PINNING**

- R phase comparator input, reference
- V phase comparator input
- STB strobe input
- TCA timing capacitor C<sub>A</sub> pin
- TCB timing capacitor C<sub>B</sub> pin
- TCC timing capacitor C<sub>C</sub> pin
- TRA biasing pin (resistor R<sub>A</sub>)
- PC<sub>1</sub> analogue phase comparator output
- PC<sub>2</sub> digital phase comparator output
- MOD phase modulation input
- OL out-of-lock indication
- OSC reference oscillator/buffer input
- XTAL reference oscillator/buffer output
- A<sub>0</sub> to A<sub>9</sub> programming inputs/programmable divider
- NS<sub>0</sub>, NS<sub>1</sub> programming inputs, prescaler
- OUT reference divider output

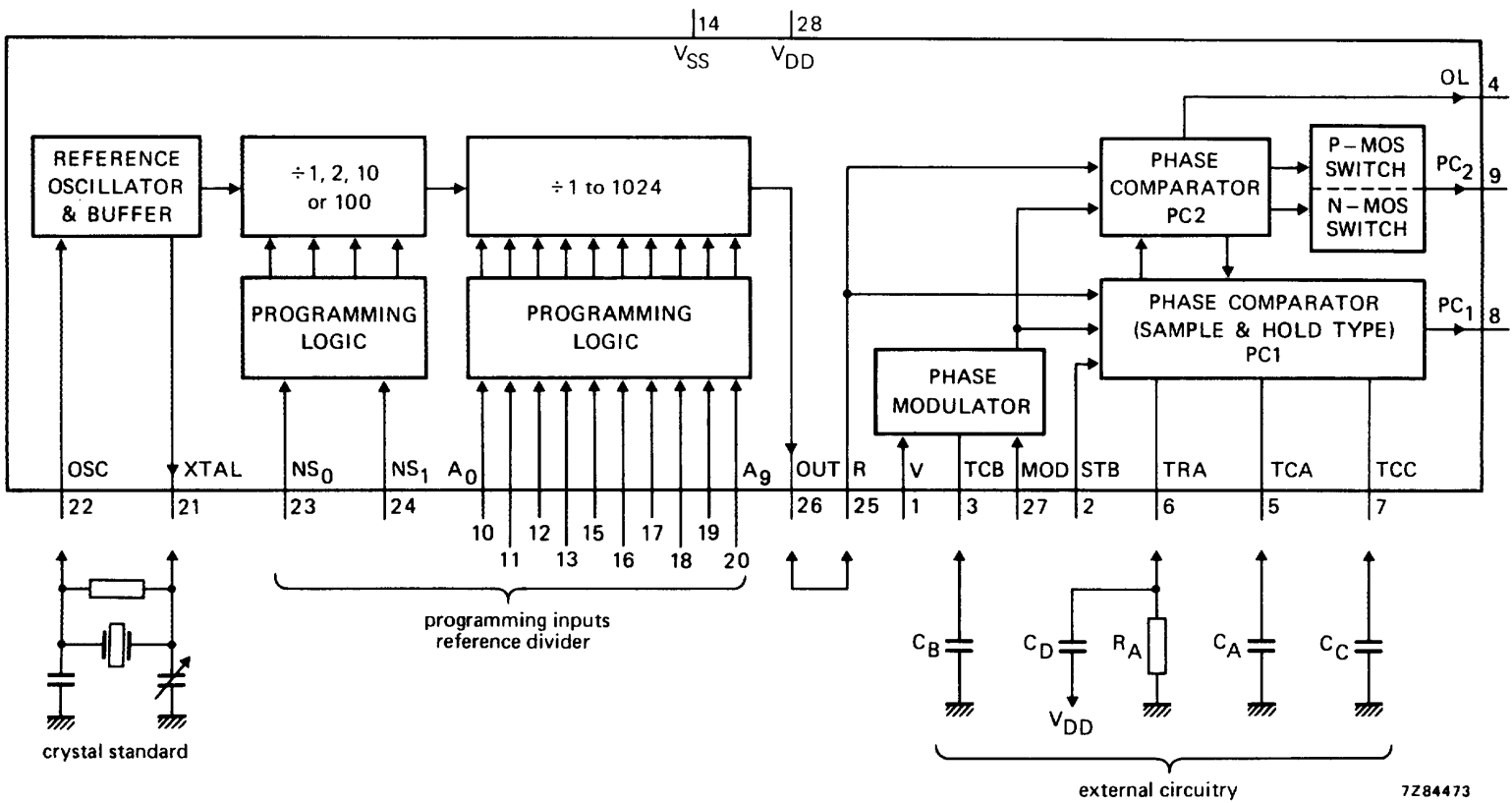
Fig.1 Pinning diagram.

HEF4750VD(F): 28-lead DIL; ceramic (cerdip)  
(SOT135)

( ): Package Designator North America

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7284473

N.B. PC<sub>1</sub> = analogue output; PC<sub>2</sub> = 3-state output.

Fig.2 Block diagram comprising five basic functions: phase comparator 1 (PC1), phase comparator 2 (PC2), phase modulator, reference oscillator and reference divider. These functions are described separately.

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## FUNCTIONAL DESCRIPTION

### Phase comparator 1

Phase comparator 1 (PC1) is built around a SAMPLE and HOLD circuit. A negative-going transition at the V-input causes the hold capacitor ( $C_A$ ) to be discharged and after a specified delay, caused by the Phase Modulator by means of an internal  $V'$  pulse, it produces a positive-going ramp. A negative-going transition at the R-input terminates

the ramp. Capacitor  $C_A$  holds the voltage that the ramp has attained. Via an internal sampling switch this voltage is transferred to  $C_C$  and in turn buffered and made available at output  $PC_1$ .

If the ramp terminates before an R-input is present, an internal end of ramp (EOR) signal is produced.

These actions are illustrated in Fig.3.

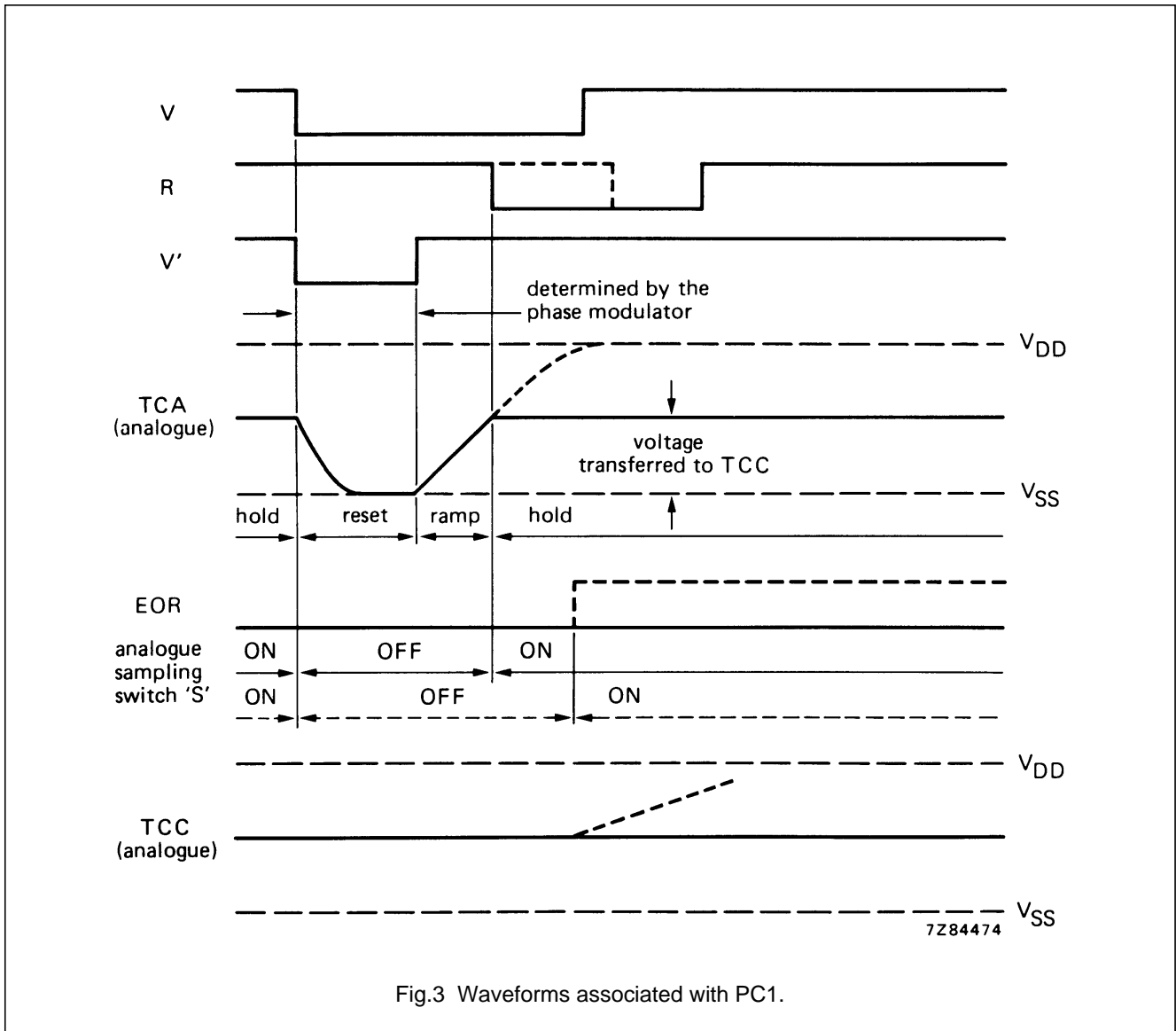
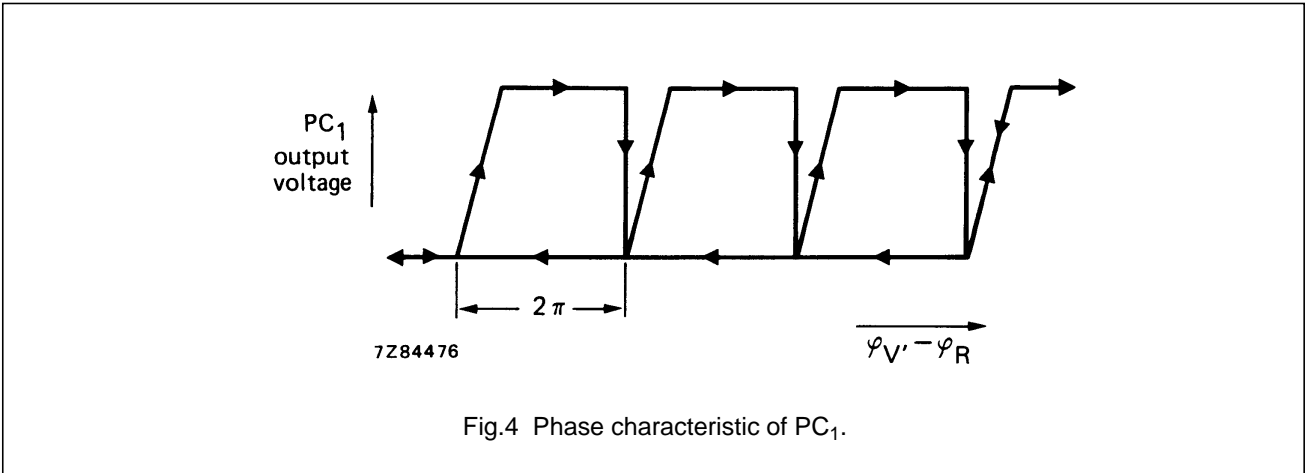


Fig.3 Waveforms associated with PC1.

The resultant phase characteristic is shown in Fig.4.

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PC1 is designed to have a high gain, typically 3200 V/cycle (at 12,5 kHz). This enables a low noise performance.

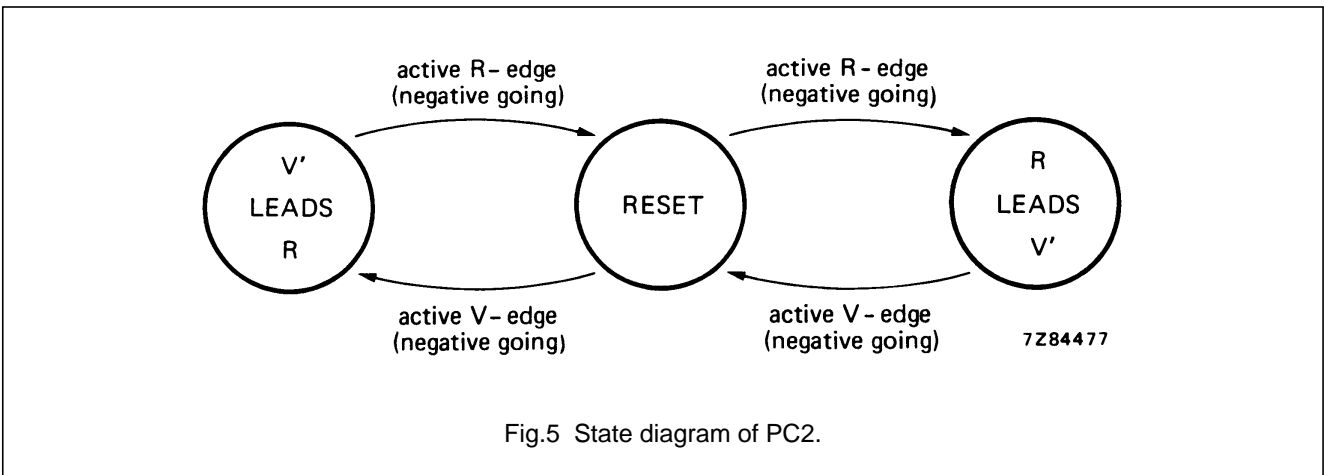
**Phase comparator 2**

Phase comparator 2 (PC2) has a wide range, which enables faster lock times to be achieved than otherwise would be possible. It has a linear  $\pm 360^\circ$  phase range, which corresponds to a gain of typically 5 V/cycle.

This digital phase comparator has three stable states:

- reset state,
- V' leads R state,
- R leads V' state.

Conversion from one state to another takes place according to the state diagram of Fig.5.



Output PC<sub>2</sub> produces positive or negative-going pulses with variable width; they depend on the phase relationship of R and V'. The average output voltage is a linear function of the phase difference. Output PC<sub>2</sub> remains in the high impedance OFF-state in the region in which PC1 operates. The resultant phase characteristic is shown in Fig.6.

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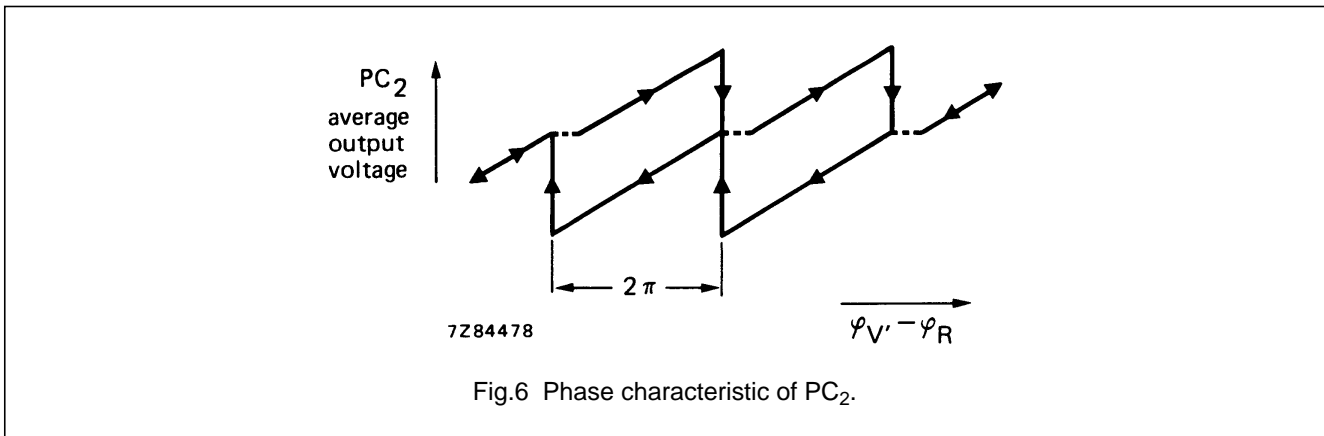


Fig.6 Phase characteristic of PC<sub>2</sub>.

**Strobe function**

The strobe function is intended for applications requiring extremely fast lock times. In normal operation the additional strobe input (STB) can be connected to the V-input and the circuit will function as described in the previous sections.

In single, phase-locked-loop type frequency synthesizers, the comparison frequency generally used is either the nominal channel spacing or a sub-multiple. PC<sub>2</sub> runs at the higher frequency (a higher reference frequency must also be used), whilst strobing takes place on the lower frequency, thereby obtaining a decrease in lock time. In a system using the Universal Divider HEF4751V, the output OFS cycles on the lower frequency, the output OFF cycles on the higher frequency.

**Out-of-lock function**

There are a number of situations in which the system goes from the locked to the out-of-lock state (OL goes HIGH):

1. When V' leads R, however out of the range of PC<sub>1</sub>.
2. When R leads V'.
3. When an R-pulse is missing.
4. When a V-pulse is missing.
5. When two successive STB-commands occur, the first without corresponding V-signal.

**Phase modulator**

The phase modulator only uses one external capacitor, C<sub>B</sub> at pin TCB. A negative-going transition at the V-input causes C<sub>B</sub> to produce a positive-going linear ramp. When the ramp has reached a value almost equal to the modulation input voltage (at MOD), the ramp terminates, C<sub>B</sub> discharges and a start signal to the C<sub>A</sub>-ramp at TCA is produced. A linear phase modulation is reached in this

way. If no modulation is required, the MOD-input must be connected to a fixed voltage of a certain positive value up to V<sub>DD</sub>. Care must be taken that the V' pulse is never smaller than the minimum value to ensure that the external capacitor of PC<sub>1</sub> (C<sub>A</sub>) can be discharged during that time. Since the V' pulse width is directly related to the TCB ramp duration, there is a requirement for the minimum value of this ramp duration.

**Reference oscillator**

The reference oscillator normally operates with an external crystal as shown in Fig.2. The internal circuitry can be used as a buffer amplifier in case an external reference should be required.

**Reference divider**

The reference divider consists of a binary divider with a programmable division ratio of 1 to 1024 and a prescaler with selectable division ratios of 1, 2, 10 and 100, according to the following tables:

**Binary divider**

N (A <sub>0</sub> TO A <sub>9</sub> )	DIVISION RATIO
0	1024
0 ≤ N ≤ 1023	N

**Prescaler**

PROGRAMMING WORD (NS <sub>0</sub> , NS <sub>1</sub> )	DIVISION RATIO
0	1
1	2
2	10
3	100

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In this way suitable comparison frequencies can be obtained from a range of crystal frequencies. The divider can also be used as a 'stand alone' programmable divider by connecting input TRA to  $V_{DD}$ , which causes all internal analogue currents to be switched off.

**Biasing circuitry**

The biasing circuitry uses an external current source or resistor, which has to be connected between the TRA and  $V_{SS}$  pins. This circuitry supplies all analogue parts of the circuit. Consequently the analogue properties of the device, such as gain, charge currents, speed, power dissipation, impedance levels etc., are mainly determined by the value of the input current at TRA. The TRA input must be decoupled to  $V_{DD}$ , as shown in Fig.7. The value of  $C_D$  has to be chosen such that the TRA input is 'clean', e.g. 10 nF at  $R_A = 68 \text{ k}\Omega$ .

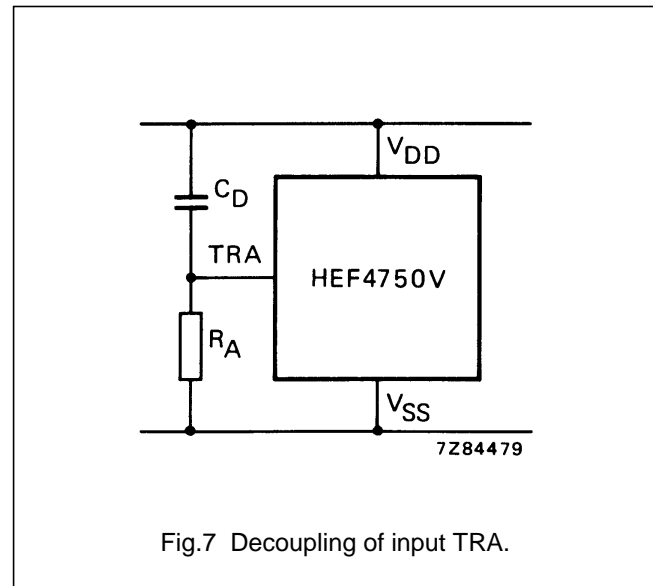


Fig.7 Decoupling of input TRA.

**RATINGS**

Limiting values in accordance with the Absolute Maximum System (IEC 134)

Supply voltage	$V_{DD}$	-0,5 to + 15 V
Voltage on any input	$V_I$	-0,5 to $V_{DD} + 0,5$ V
D.C. current into any input or output	$\pm I$	max. 10 mA
Power dissipation per package for $T_{amb} = 0$ to + 85 °C	$P_{tot}$	max. 500 mW
Power dissipation per output for $T_{amb} = 0$ to 85 °C	$P$	max. 100 mW
Storage temperature	$T_{stg}$	-65 to + 150 °C
Operating ambient temperature	$T_{amb}$	-40 to + 85 °C



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## DC CHARACTERISTICS

at  $V_{DD} = 10\text{ V} \pm 5\%$ ; voltages are referenced to  $V_{SS} = 0\text{ V}$ , unless otherwise specified; for definitions see note 1.

PARAMETER	SYMBOL	$T_{amb}$ (°C)									UNIT	NOTES
		-40			+ 25			+ 85				
		MIN.	TYP.	MAX.	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.		
Quiescent device current	$I_{DD}$	-	-	100	-	-	100	-	-	750	$\mu\text{A}$	2
Input current; logic inputs, MOD	$\pm I_{IN}$	-	-	300	-	-	300	-	-	1000	nA	3
Output leakage current at $\frac{1}{2} V_{DD}$												
TCA, hold-state	$\pm I_Z$	-	-	20	-	0,05	20	-	-	60	nA	3,4
TCC, analogue switch OFF	$\pm I_Z$	-	-	20	-	0,05	20	-	-	60	nA	
PC <sub>2</sub> , high impedance OFF-state	$\pm I_Z$	-	-	50	-	-	50	-	-	500	nA	
Logic input voltage LOW	$V_{IL}$	_____ max. $0,3 V_{DD}$ _____									V	
HIGH	$V_{IH}$	_____ max. $0,7 V_{DD}$ _____									V	
Logic output voltage LOW; at $ I_O  < 1\ \mu\text{A}$	$V_{OL}$	-	-	50	-	-	50	-	-	50	mV	3
HIGH	$V_{OH}$	_____ min. $V_{DD} - 50\text{ mV}$ _____									mV	3
Logic output current LOW; at $V_{OL} = 0,5\text{ V}$ outputs OL, PC <sub>2</sub> , OUT	$I_{OL}$	5,5	-	-	4,6	-	-	3,6	-	-	mA	3
output XTAL	$I_{OL}$	2,8	-	-	2,4	-	-	1,9	-	-	mA	
Logic output current HIGH; at $V_{OH} = V_{DD} - 0,5\text{ V}$ outputs OL, PC <sub>2</sub> , OUT	$-I_{OH}$	1,5	-	-	1,3	-	-	1,0	-	-	mA	3
output XTAL	$-I_{OH}$	1,4	-	-	1,2	-	-	0,9	-	-	mA	
Output TCC sink current	$I_O$	-	-	-	-	2,1	-	-	-	-	mA	3,4,5
Output TCC source current	$-I_O$	-	-	-	-	1,9	-	-	-	-	mA	3,4,6
Internal resistance of TCC   output swing   $\leq 200\text{ mV}$ specified output range: $0,3 V_{DD}$ to $0,7 V_{DD}$	$R_i$	-	-	-	-	0,7	-	-	-	-	k $\Omega$	3,4

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PARAMETER	SYMBOL	$T_{amb}$ (°C)									UNIT	NOTES
		-40			+ 25			+ 85				
		MIN.	TYP.	MAX.	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.		
Output TCC voltage with respect to TCA input voltage	$\Delta V$	-	0	-	-	0	-	-	0	-	V	3,4,7
Output PC <sub>1</sub> sink current	$I_o$	-	-	-	-	1,1	-	-	-	-	mA	3,4,8
Output PC <sub>1</sub> source current	$-I_o$	-	-	-	-	1,0	-	-	-	-	mA	3,4,9
Internal resistance of PC <sub>1</sub>   output swing   $\leq 200$ mV specified output range: 0,3 $V_{DD}$ to 0,7 $V_{DD}$	$R_i$	-	-	-	-	1,4	-	-	-	-	k $\Omega$	3,4
Output PC <sub>1</sub> voltage with respect to TCC input voltage	$\Delta V$	-	0	-	-	0	-	-	0	-	V	3,4,10
EOR generation $V_{EOR} = V_{DD} - V_{TCA}$	$V_{EOR}$	-	0,9	-	-	0,7	-	-	0,6	-	V	3,4,11
Source current; HIGH at $V_{OUT} = \frac{1}{2} V_{DD}$ ; output in ramp mode												3,4
TCA	$I_o$	-	-	-	-	13	-	-	-	-	mA	
TCB	$I_o$	-	-	-	-	2,5	-	-	-	-	mA	

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## AC CHARACTERISTICS

## General note

The dynamic specifications are given for the circuit built-up with external components as given in Fig.8, under the following conditions; for definitions see note 1; for definitions of times see Fig.19;  $V_{DD} = 10\text{ V} \pm 5\%$ ;  $T_{amb} = 25\text{ }^{\circ}\text{C}$ ; input transition times  $\leq 20\text{ ns}$ ;  $R_A = 68\text{ k}\Omega \pm 30\%$  (see also note 4);  $C_A = 270\text{ pF}$ ;  $C_B = 150\text{ pF}$ ;  $C_C = 1\text{ nF}$ ;  $C_D = 10\text{ nF}$ ; unless otherwise specified.

	SYMBOL	MIN.	TYP.	MAX.	UNIT	CONDITIONS	NOTES
Slew rate							
TCA	$S_{TCA}$	–	52	–	V/ $\mu$ s	$R_A = \text{minimum}$	12
TCA	$S_{TCA}$	–	28	–	V/ $\mu$ s	$R_A = \text{maximum}$	12
TCB	$S_{TCB}$	–	20	–	V/ $\mu$ s	$R_A = \text{minimum}$	12
TCB	$S_{TCB}$	–	10	–	V/ $\mu$ s	$R_A = \text{maximum}$	12
Ramp linearity							
TCA	$I_{TCA}$	–	2	–	%		13
TCB	$I_{TCB}$	–	2	–	%		13
Start of TCA-ramp delay	$t_{CBCA}$	–	200	–	ns		
Delay of TCA-hold	$t_{RCA}$	–	40	–	ns		
Delay of TCA-discharge	$t_{VCA}$	–	60	–	ns		
Start of TCB-ramp delay	$t_{VCB}$	–	60	–	ns		
TCB-ramp duration	$t_{rCB}$	–	250	–	ns	$V_{MOD} = 4\text{ V}$	
	$t_{rCB}$	–	350	–	ns	$V_{MOD} = 6\text{ V}$	
	$t_{rCB}$	–	450	–	ns	$V_{MOD} = 8\text{ V}$	
Required TCB min. ramp duration	$t_{rCB}$	–	150	–	ns		14
Pulse width							
V : LOW	$t_{PWVL}$	–	20	–	ns		
V : HIGH	$t_{PWVH}$	–	20	–	ns		
R : LOW	$t_{PWRL}$	–	20	–	ns		
R : HIGH	$t_{PWRH}$	–	20	–	ns		
STB : LOW	$t_{PWSL}$	–	20	–	ns		
STB : HIGH	$t_{PWSH}$	–	20	–	ns		
Fall time							
TCA	$t_{fCA}$	–	50	–	ns		
TCB	$t_{fCB}$	–	50	–	ns		
Prescaler input frequency	$f_{PR}$	–	30	–	MHz	all division ratios	
Binary divider frequency	$f_{DIV}$	–	30	–	MHz	all division ratios	
Crystal oscillator frequency	$f_{OSC}$	–	10	–	MHz		
Average power supply current						locked state	
with speed-up 1 : 10	$I_P$	–	3,6	–	mA		15
without speed-up	$I_P$	–	3,2	–	mA		16

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**Notes**

## 1. Definitions:

$R_A$  = external biasing resistor between pins TRA and  $V_{SS}$ ;  $68\text{ k}\Omega \pm 30\%$ .

$C_A$  = external timing capacitor for time/voltage converter, between pins TCA and  $V_{SS}$ .

$C_B$  = external timing capacitor for phase modulator, between pins TCB and  $V_{SS}$ .

$C_C$  = external hold capacitor between pins TCC and  $V_{SS}$ .

$C_D$  = decoupling capacitor between pins TRA and  $V_{DD}$ .

Logic inputs: V, R, STB,  $A_0$  to  $A_9$ ,  $NS_0$ ,  $NS_1$ , OSC.

Logic outputs: OL,  $PC_2$ , XTAL, OUT.

Analogue signals: TCA, TCB, TCC, TRA,  $PC_1$ , MOD.

2. TRA at  $V_{DD}$ ; TCA, TCB, TCC and MOD at  $V_{SS}$ ; logic inputs at  $V_{SS}$  or  $V_{DD}$ .

3. All logic inputs at  $V_{SS}$  or  $V_{DD}$ .

4.  $R_A$  connected; its value chosen such that  $I_{TRA} = 100\ \mu\text{A}$ .

5. The analogue switch is in the ON position (see Fig.9).

6. The analogue switch is in the ON position (see Fig.10).

7. See Fig.11.

This guarantees the d.c. voltage gain, combined with d.c.-offset.

Input condition:  $0,3\ V_{DD} \leq V_{TCA} \leq 0,7\ V_{DD}$ .

$\Delta V = V_{TCC} - V_{TCA}$ .

8. See Fig.12.

9. See Fig.13.

10. See Fig.14.

This guarantees the d.c. voltage gain, combined with d.c.-offset.

Input condition:  $0,3\ V_{DD} \leq V_{TCC} \leq 0,7\ V_{DD}$ .

$\Delta V = V_{PC1} - V_{TCC}$ .

11. Switching level at TCA, generating an EOR-signal, during increasing input voltage.

12. See Fig.15.

13. See Fig.16.

Definition of the ramp linearity at full swing.

14. The external components and modulation input voltage must be chosen such that this requirement will be fulfilled, to ensure that  $C_A$  is sufficiently discharged during that time.

15. See Fig.17.

Circuit connections for power supply current specification, with speed-up 1 : 10. V and R are in the range of  $PC_1$ , such that the output voltage at  $PC_1$  is equal to 5 V.

$f_{OSC} = 5\ \text{MHz}$  (external clock)

$f_{STB} = 12,5\ \text{kHz}$

$f_V = 125\ \text{kHz}$

16. See Fig.18.

Circuit connections for power supply current specification, without speed-up. V and R are in the range of  $PC_1$ , such that the output voltage at  $PC_1$  is equal to 5 V.

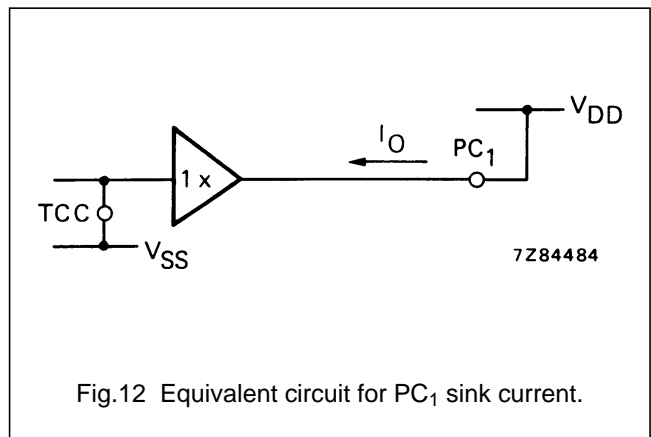
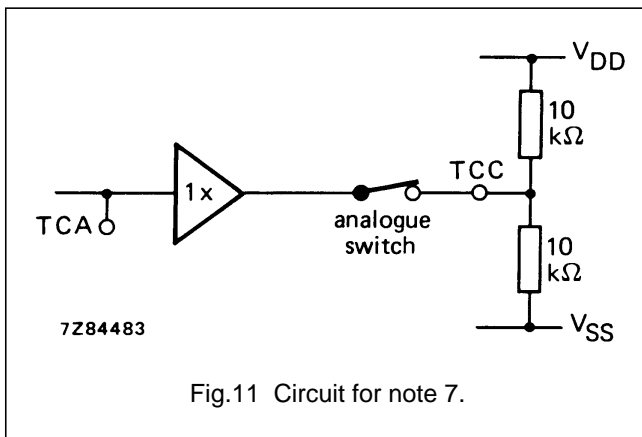
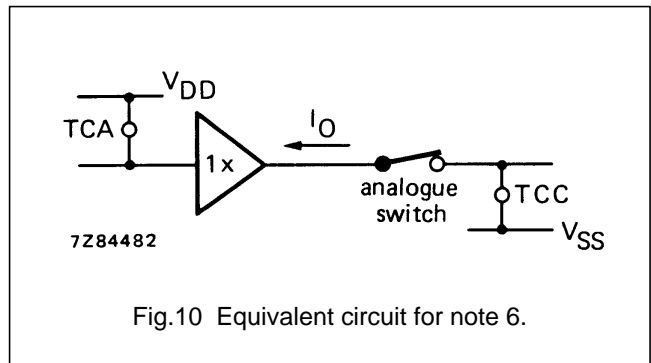
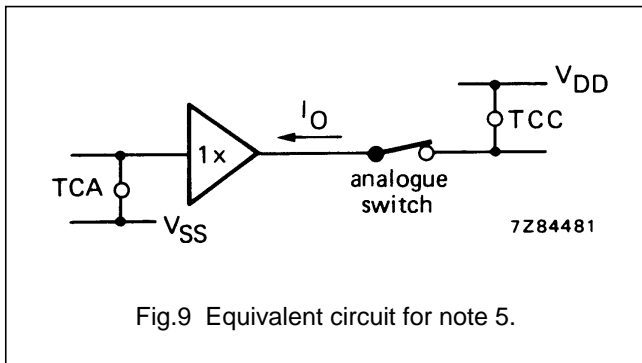
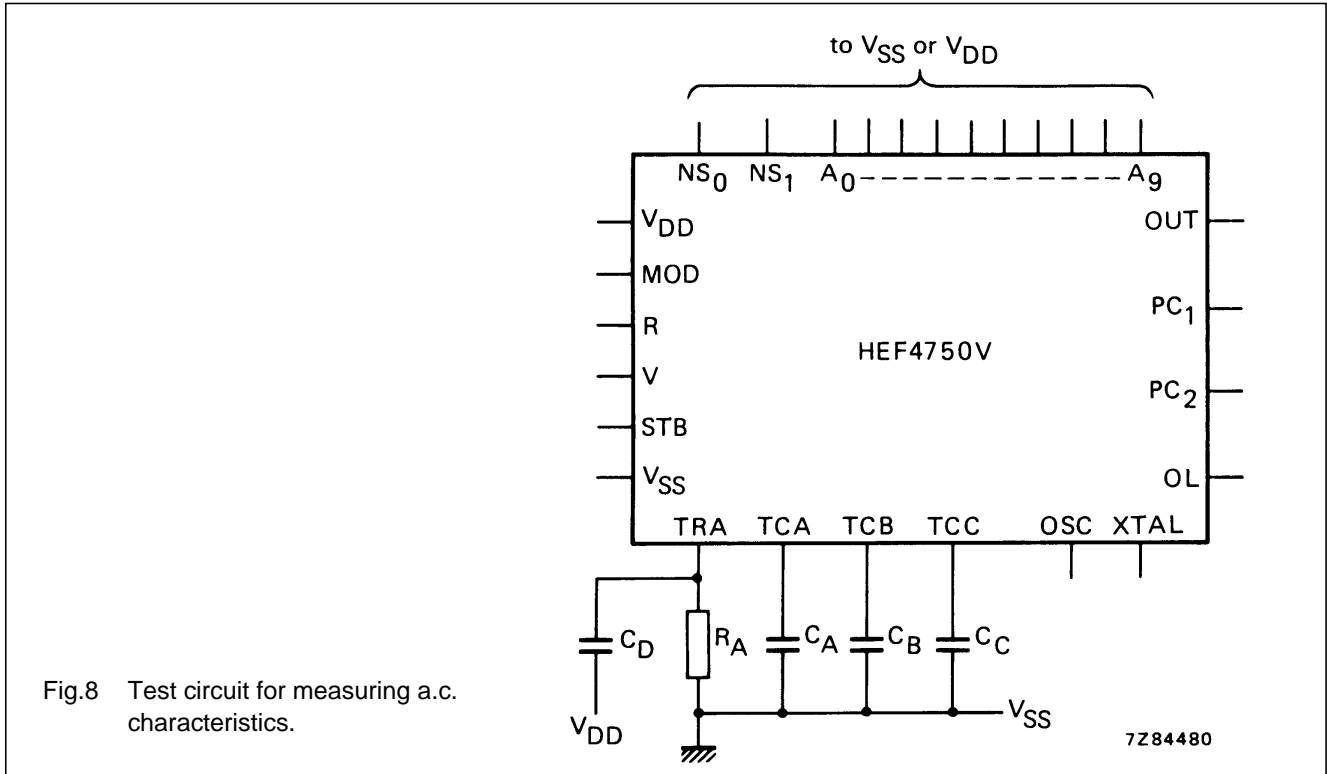
$f_{OSC} = 5\ \text{MHz}$  (external clock)

$f_{STB} = 12,5\ \text{kHz}$

$f_V = 12,5\ \text{kHz}$

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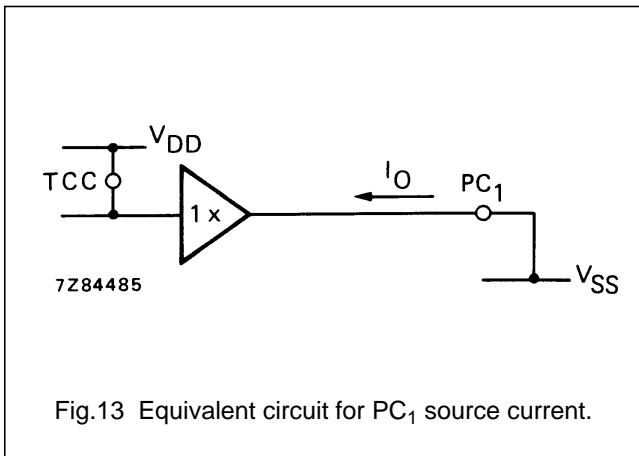


Fig.13 Equivalent circuit for PC<sub>1</sub> source current.

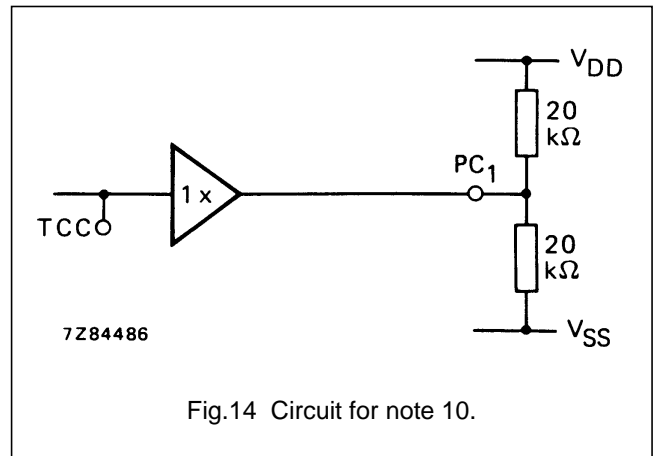


Fig.14 Circuit for note 10.

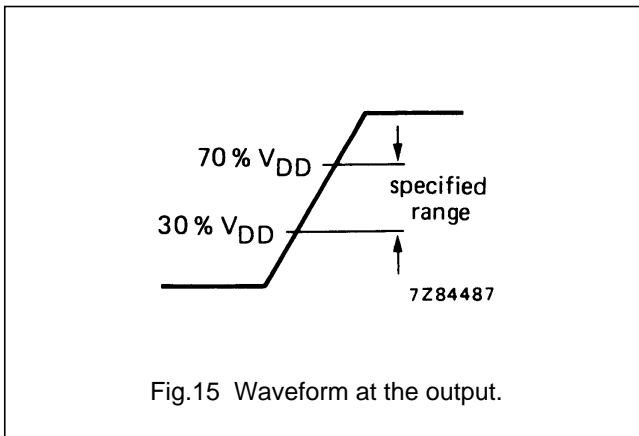


Fig.15 Waveform at the output.

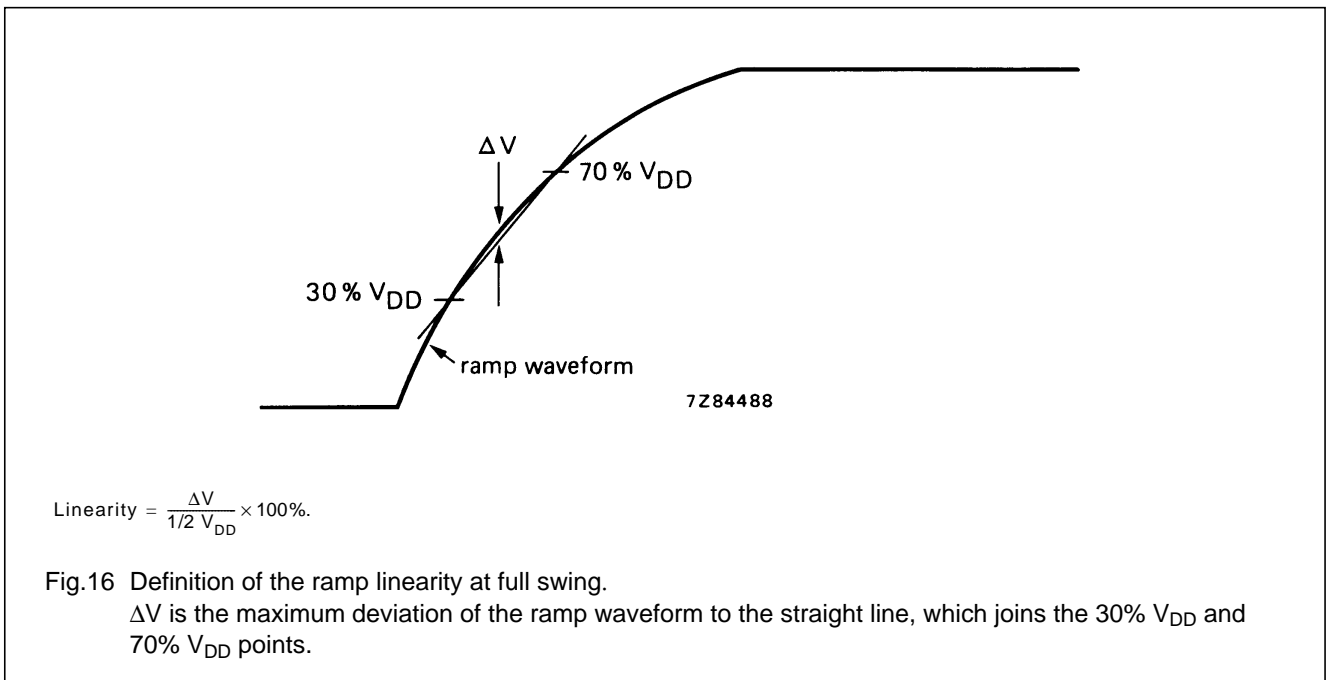


Fig.16 Definition of the ramp linearity at full swing.  
 $\Delta V$  is the maximum deviation of the ramp waveform to the straight line, which joins the 30%  $V_{DD}$  and 70%  $V_{DD}$  points.

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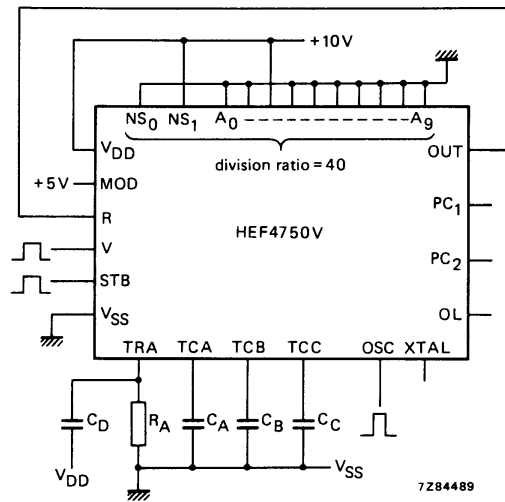


Fig.17 Circuit for note 15.

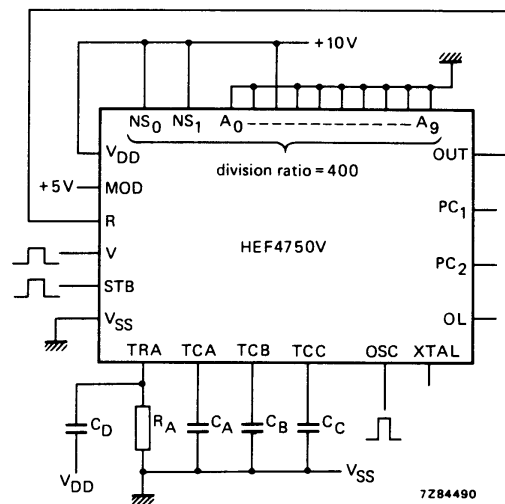
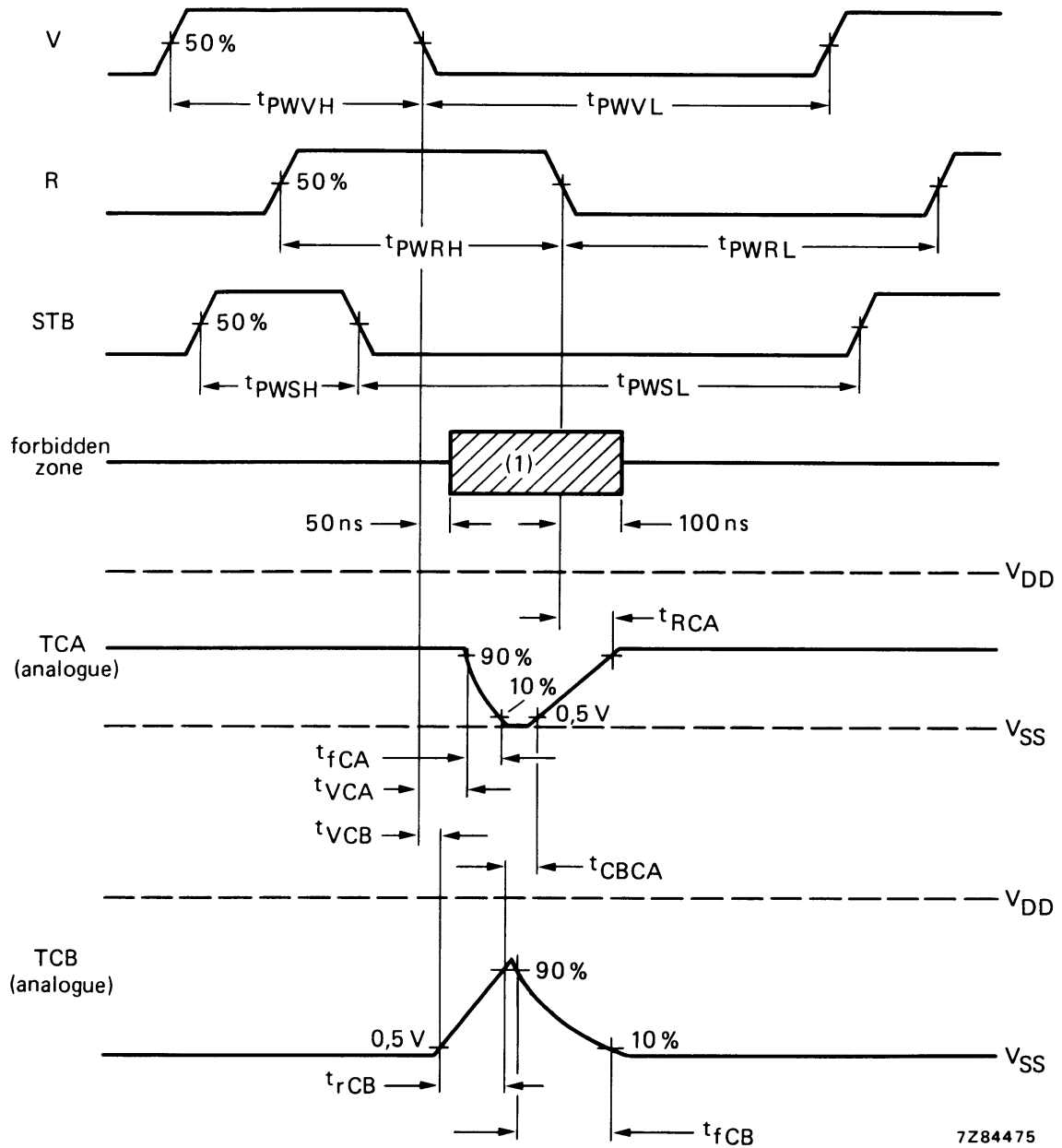


Fig.18 Circuit for note 16.

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(1) Forbidden zone in the *locked state* for the positive edge of V and R and both edges of STB.

Fig.19 Waveforms showing times in the locked state.



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APPLICATION INFORMATION

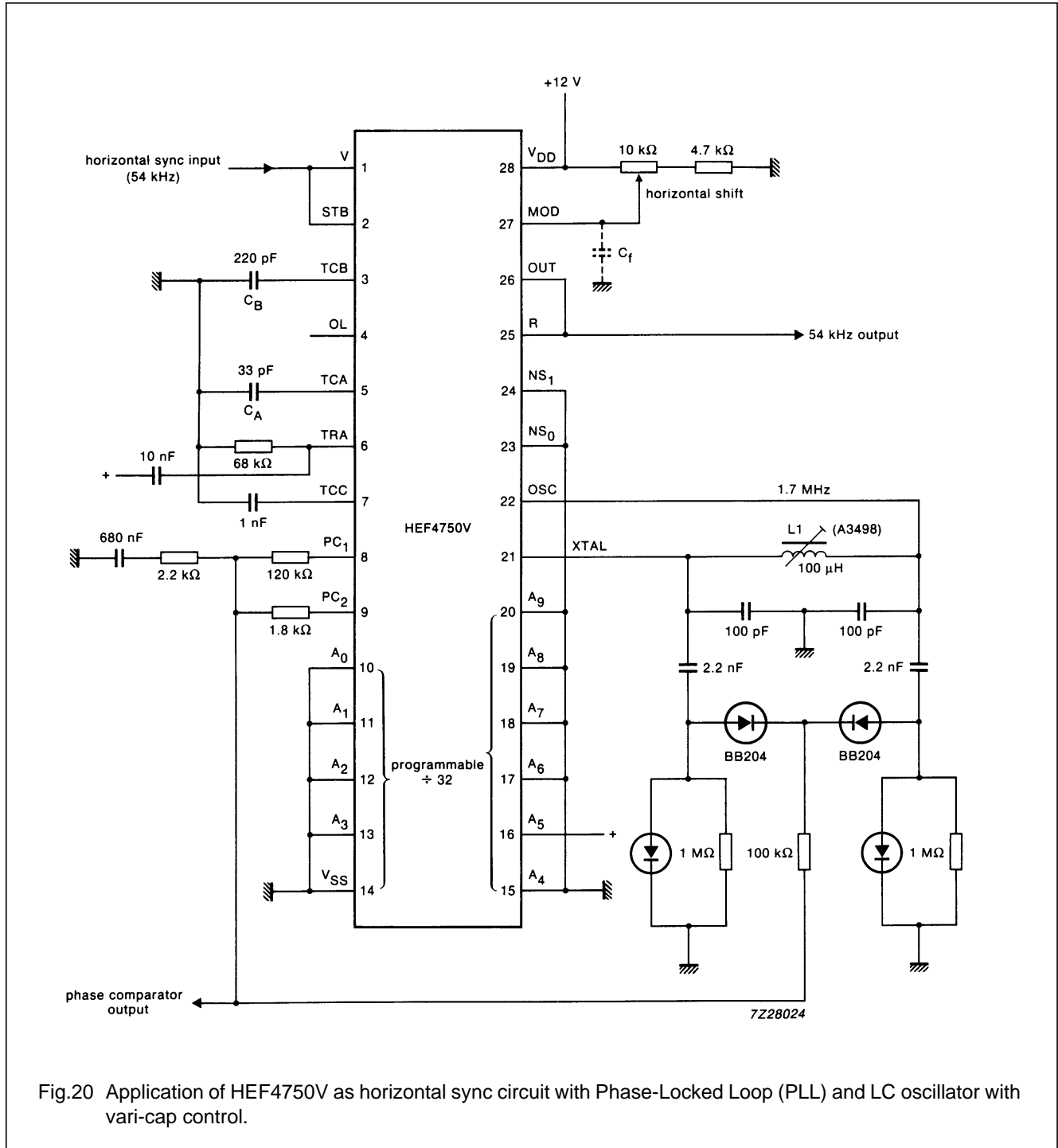


Fig.20 Application of HEF4750V as horizontal sync circuit with Phase-Locked Loop (PLL) and LC oscillator with vari-cap control.